

Transistors

1.5V Drive Pch MOSFET

RZQ045P01

●Structure

Silicon P-channel MOSFET

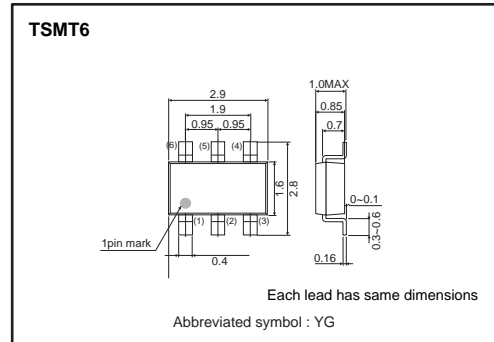
●Features

- 1) Low on-resistance.
- 2) High power package.
- 3) Low voltage drive. (1.5V)

●Applications

Switching

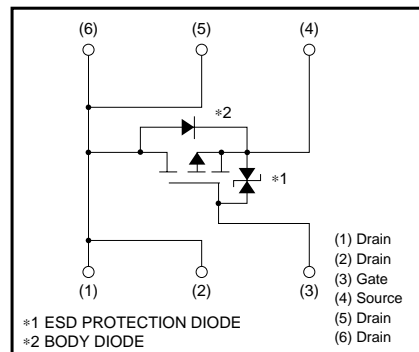
●Dimensions (Unit : mm)



●Packaging specifications

| Type | Package | Taping |
|-----------|------------------------------|--------|
| | Code | TR |
| | Basic ordering unit (pieces) | 3000 |
| RZQ045P01 | | ○ |

●Equivalent circuit



●Absolute maximum ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit | |
|------------------------------|-------------------|--------------------|------|---|
| Drain-source voltage | V _{DSS} | -12 | V | |
| Gate-source voltage | V _{GSS} | ±10 | V | |
| Drain current | Continuous | I _D | ±4.5 | A |
| | Pulsed | I _{DP} *1 | ±12 | A |
| Source current (Body diode) | Continuous | I _S | -1 | A |
| | Pulsed | I _{SP} *1 | -12 | A |
| Total power dissipation | P _D *2 | 1.25 | W | |
| Channel temperature | T _{ch} | 150 | °C | |
| Range of Storage temperature | T _{stg} | -55 to +150 | °C | |

*1 Pw≤10μs, Duty cycle≤1%
*2 Mounted on a ceramic board

●Thermal resistance

| Parameter | Symbol | Limits | Unit |
|--------------------|-------------------------|--------|--------|
| Channel to ambient | R _{th(ch-a)} * | 100 | °C / W |

* Mounted on a ceramic board.

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●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|----------------|------|------|------|------|------------------------------------|
| Gate-source leakage | I_{GSS} | – | – | ±10 | μA | $V_{GS}=\pm 10V, V_{DS}=0V$ |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | –12 | – | – | V | $I_D = -1mA, V_{GS}=0V$ |
| Zero gate voltage drain current | I_{DSS} | – | – | –1 | μA | $V_{DS} = -12V, V_{GS}=0V$ |
| Gate threshold voltage | $V_{GS(th)}$ | –0.3 | – | –1.0 | V | $V_{DS} = -6V, I_D = -1mA$ |
| Static drain-source on-state resistance | $R_{DS(on)}$ * | – | 25 | 35 | mΩ | $I_D = -4.5A, V_{GS} = -4.5V$ |
| | | – | 31 | 43 | mΩ | $I_D = -2.2A, V_{GS} = -2.5V$ |
| | | – | 39 | 58 | mΩ | $I_D = -2.2A, V_{GS} = -1.8V$ |
| | | – | 50 | 100 | mΩ | $I_D = -0.9A, V_{GS} = -1.5V$ |
| Forward transfer admittance | $ Y_{fs} $ * | 6.5 | – | – | S | $V_{DS} = -6V, I_D = -4.5A$ |
| Input capacitance | C_{iss} | – | 2450 | – | pF | $V_{DS} = -6V$ |
| Output capacitance | C_{oss} | – | 320 | – | pF | $V_{GS} = 0V$ |
| Reverse transfer capacitance | C_{rss} | – | 290 | – | pF | $f = 1MHz$ |
| Turn-on delay time | $t_{d(on)}$ * | – | 12 | – | ns | $I_D = -2.2A$ |
| Rise time | t_r * | – | 75 | – | ns | $V_{DD} = -6V$ $V_{GS} = -4.5V$ |
| Turn-off delay time | $t_{d(off)}$ * | – | 390 | – | ns | $R_L = 2.7\Omega$ |
| Fall time | t_f * | – | 215 | – | ns | $R_G = 10\Omega$ |
| Total gate charge | Q_g * | – | 31 | – | nC | $V_{DD} = -6V, R_L = 1.3\Omega$ |
| Gate-source charge | Q_{gs} * | – | 4.5 | – | nC | $V_{GS} = -4.5V, R_G = 10\Omega$ |
| Gate-drain charge | Q_{gd} * | – | 4.0 | – | nC | $I_D = -4.5A$ |

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-----------------|------------|------|------|------|------|----------------------------|
| Forward voltage | V_{SD} * | – | – | –1.2 | V | $I_S = -4.5A, V_{GS} = 0V$ |

*Pulsed

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●Electrical characteristic curves

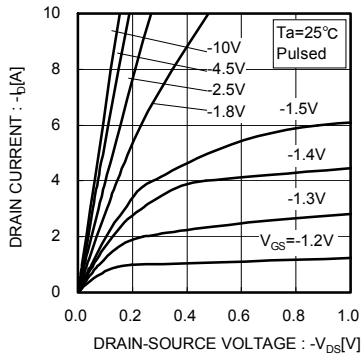


Fig.1 Typical Output Characteristics(I)

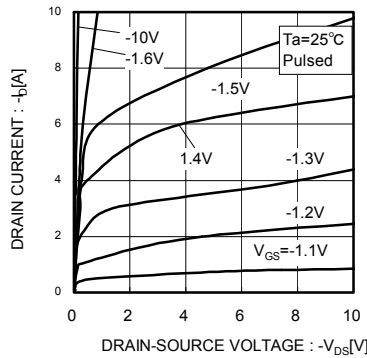


Fig.2 Typical Output Characteristics(II)

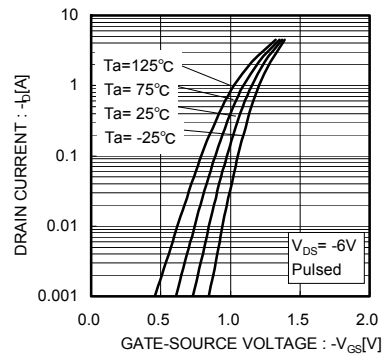


Fig.3 Typical Transfer Characteristics

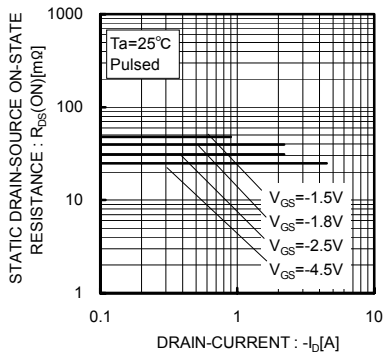


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

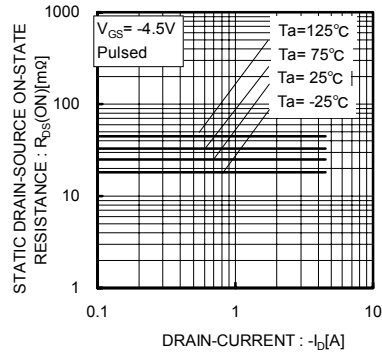


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

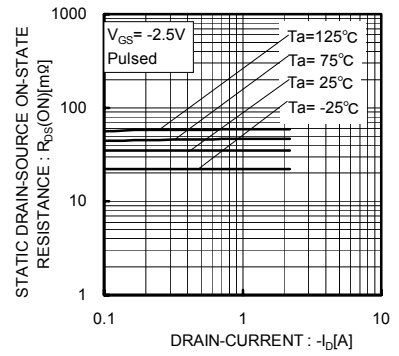


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

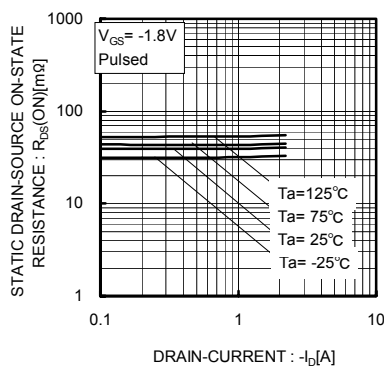


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

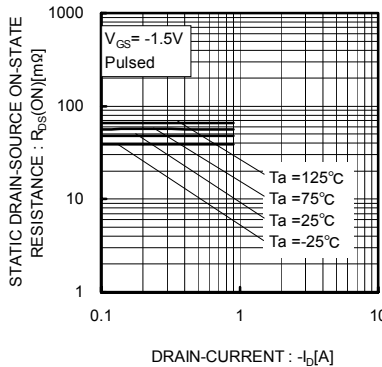


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

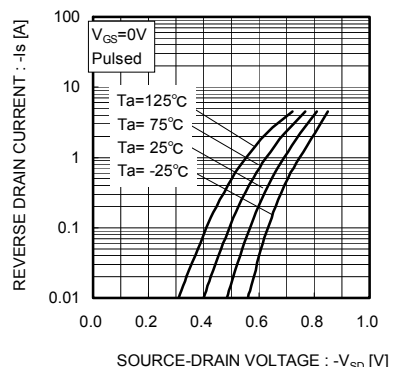


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

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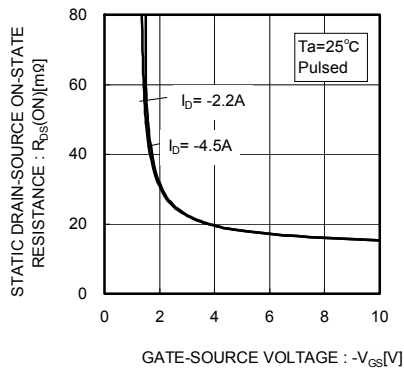


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

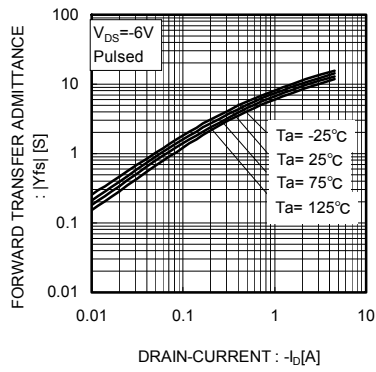


Fig.11 Forward Transfer Admittance vs. Drain Current

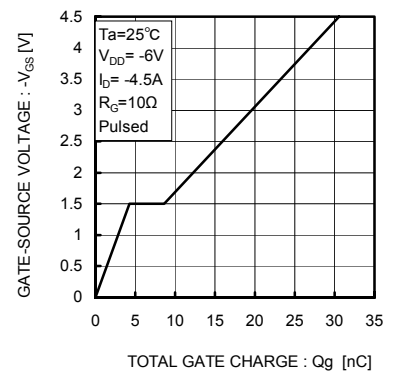


Fig.12 Dynamic Input Characteristics

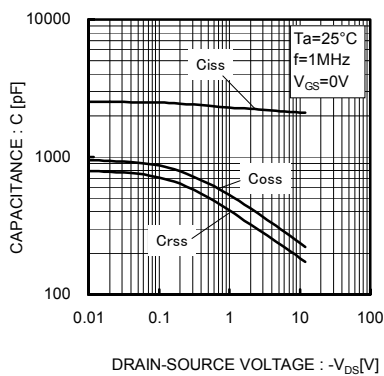


Fig.13 Typical Capacitance vs. Drain-Source Voltage

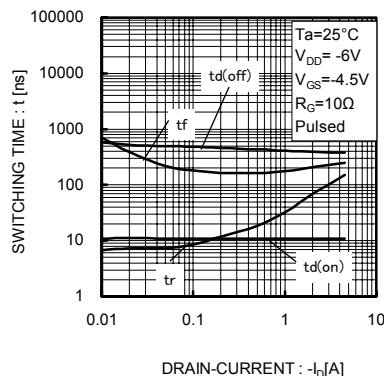


Fig.14 Switching Characteristics

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●Measurement circuits

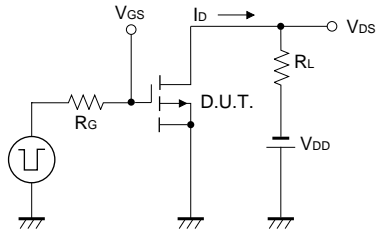


Fig.15 Switching Time Measurement Circuit

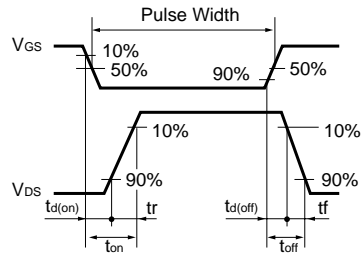


Fig.16 Switching Waveforms

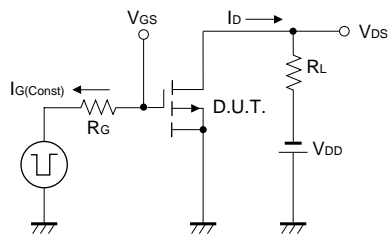


Fig.17 Gate Charge Measurement Circuit

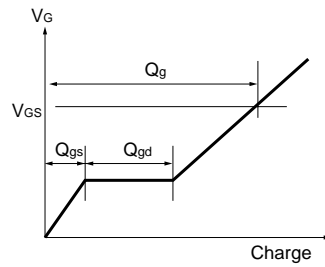


Fig.18 Gate Charge Waveform

●Notice

This product might cause chip aging and breakdown under the large electrified environment .
Please consider to design ESD protection circuit.

Notes

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